

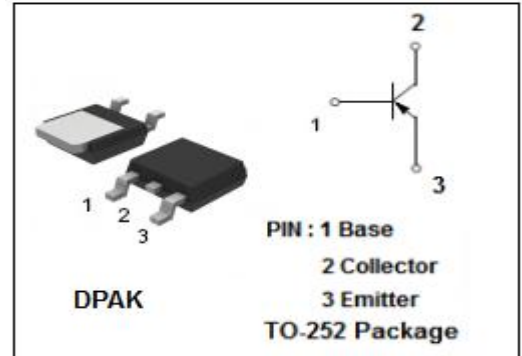
Silicon PNP Power Transistors

DESCRIPTION

- Low Collector Saturation Voltage
- High Power Dissipation-
: $P_C = 10W(\text{Max})@T_C = 25^\circ\text{C}$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

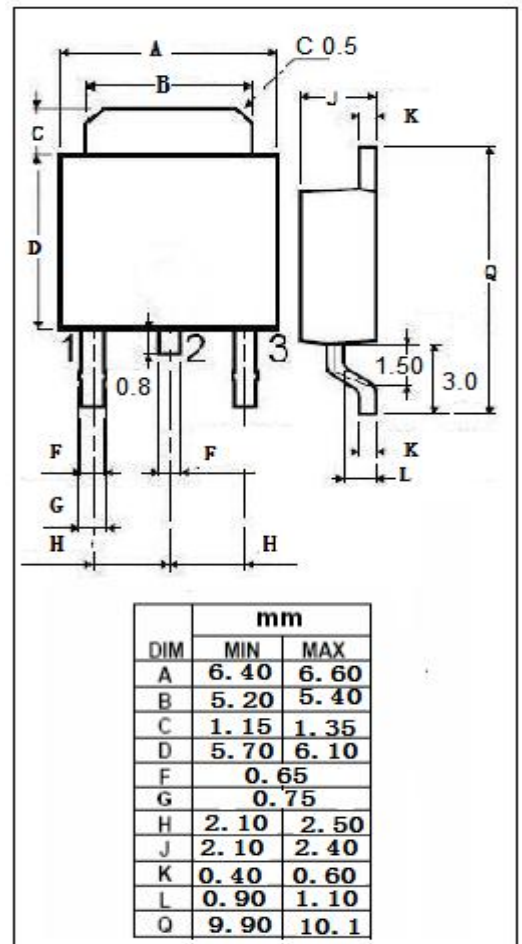
APPLICATIONS

- Designed for use in audio amplifier and switching, especially in hybrid integrated circuits.



ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-3	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	10	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS
T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = -100 μ A; I _E = 0	-60			V
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -1mA; I _B = 0	-60			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -100 μ A; I _C = 0	-7			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -1.5A; I _B = -0.15A			-0.3	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = -1.5A; I _B = -0.15A			-1.2	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -60V; I _E = 0			-10	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -7V; I _C = 0			-10	μ A
h _{FE-1}	DC Current Gain	I _C = -0.2A; V _{CE} = -2V	60			
h _{FE-2}	DC Current Gain	I _C = -0.6A; V _{CE} = -2V	100		400	
h _{FE-3}	DC Current Gain	I _C = -2A; V _{CE} = -2V	50			

◆ h_{FE2} Classifications

M	L	K
100-200	160-320	200-400